

IN THE CLAIMS:

1. (Currently Amended) A semiconductor manufacturing apparatus comprising:
[[a]] means for transferring an object to be processed [[,]] ;
at least one plasma generating means for performing a plasma treatment; film formation treatment, etching treatment or ashing treatment, and
means for moving the plasma generating means in the intersecting direction with a transferring direction of the object to be processed [[,]] .

~~wherein the film formation treatment, the etching treatment or the ashing treatment is performed on the object to be processed by transferring the object to be processed and a movement of the plasma generating means.~~

2. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the plasma treatment is performed by the plasma generating means ~~has a structure which is performed~~ under atmospheric pressure or adjacent to atmospheric pressure.

3. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the means for transferring the object to be processed ~~has a structure to transfer~~ transfers the object to be processed unidirectionally.

4. (Currently Amended) A semiconductor manufacturing apparatus according to claim 1, wherein the object is transferred continuously or with the use of step-feed by the means for transferring the object to be processed, ~~has a structure to perform continuous or step feed~~.

5. (Original) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment,

wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed, and

wherein film formation treatment, etching treatment or ashing treatment is performed on the object to be processed by transferring of the object to be processed and generating plasma in at least one of the plurality of plasma generating means.

6. (Original) A semiconductor manufacturing apparatus according to claim 5, wherein the plasma generating means has a structure which is performed under atmospheric pressure or adjacent to atmospheric pressure.

7. (Original) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

8. (Original) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

9. (Currently Amended) A semiconductor manufacturing apparatus comprising:
[[a]] means for transferring an object to be processed [[,]] ;
at least one droplet spraying means for spraying a droplet ~~onto a surface of~~ to the object to be processed [[,]] ; and
[[a]] means for moving the droplet spraying means in the intersecting direction with a transferring direction of the object to be processed [[,]] .
~~wherein a droplet is attached to the object to be processed by transfer of the object to be processed and a movement of the droplet spraying means.~~

10. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the spraying of the droplet is ~~attached~~ performed to a surface of the object under atmospheric pressure or adjacent to atmospheric pressure.

11. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the means for transferring the object to be processed ~~has a structure to transfer~~ transfers the object to be processed unidirectionally.

12. (Currently Amended) A semiconductor manufacturing apparatus according to claim 9, wherein the object is transferred continuously or with the use of step-feed by the means for transferring the object, ~~the transfer of the object to be processed is continuous or step-feed~~.

13. (Original) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is an organic solvent containing organic resin or metal element.

14. (Original) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of droplet spraying means for spraying a droplet onto the surface of the object to be processed,

wherein the plurality of droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed,

and a droplet is attached to the object to be processed by the transfer of the object to be processed and spraying a droplet from at least one of the plurality of droplet spraying means.

15. (Original) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is attached under atmospheric pressure or adjacent to atmospheric pressure.

16. (Original) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

17. (Original) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

18. (Original) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is an organic solvent containing organic resin or a metal element.

19. (Currently Amended) A semiconductor manufacturing apparatus comprising:
[[a]] means for transferring an object to be processed [[,]] ;
at least one plasma generating means for performing a plasma treatment; ~~film formation treatment, etching treatment or ashing treatment, and~~
at least one droplet spraying means for attaching spraying a droplet [[on]] to the object to be processed [[,]] ;
first means for moving the plasma generating means in the intersecting direction with a transferring direction of the object; and
second means for moving the droplet spraying means in the intersection direction with the transferring direction of the object.
~~wherein the plasma generating means and the droplet spraying means have a means for moving in the intersecting direction with a transferring direction of the object to be processed,~~
~~and wherein the film formation treatment, etching treatment or ashing treatment is performed or a droplet is attached on the object to be processed by transfer of the object to be processed and a movement of the plasma generating means and the droplet spraying means.~~

20. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating means for forming a [[the]] film formation treatment over the object, [[the]] etching treatment the object or [[the]] ashing the object treatment, or the attachment of the droplet is performed under atmospheric pressure or adjacent to atmospheric pressure.

21. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the means for transferring the object to be processed ~~has a structure to transfer~~ transfers the object to be processed unidirectionally.

22. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed by the means for transferring the object to be processed, ~~has a structure to perform continuous or step-feed~~.

23. (Currently Amended) A semiconductor manufacturing apparatus according to claim 19, wherein a plurality of treatment treatments selected from the film formation forming treatment, the etching treatment, the ashing treatment or the spraying attachment treatment of the droplet are performed simultaneously.

24. (Original) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment on the object to be processed, a plurality of droplet spraying means for attaching a droplet on the object to be processed,

wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the plurality of the droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the film formation treatment, the etching treatment or the ashing treatment is performed on the object to be processed by the transfer of the object to be processed and generating plasma in at least one of the plurality of plasma generating means, and

wherein attach the droplet on the object to be processed by the transfer of the object to be processed and spraying the droplet from the droplet spraying means.

25. (Original) A semiconductor manufacturing apparatus according to claim 24, wherein the film formation treatment, the etching treatment or the attachment of the droplet is performed under atmospheric pressure or adjacent to atmospheric pressure.

26. (Original) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

27. (Original) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

28. (Original) A semiconductor manufacturing apparatus according to claim 24, wherein a plurality of treatment selected from the film formation treatment, the etching treatment, the ashing treatment or the attachment treatment of the droplet are performed simultaneously.

29. (New) A semiconductor manufacturing apparatus according to claim 1, wherein the plasma treatment is performed by the plasma generating means for forming a film over the object, etching the object, or ashing the object.

30. (New) A semiconductor manufacturing apparatus according to claim 1, wherein the plasma treatment is performed by the plasma generating means while transferring the object and moving the plasma generating means.

31. (New) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is attached onto a surface of the object to be processed while transferring the object and moving the droplet spraying means.

32. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating means under atmospheric pressure or adjacent to atmospheric pressure.

33. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating means while transferring the object and moving the plasma generating means.

34. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the spraying of the droplet is performed to a surface of the object under atmospheric pressure or adjacent to atmospheric pressure.

35. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the means for transferring the object to be processed transfers the object to be processed unidirectionally.

36. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed by the means for transferring the object.

37. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is an organic solvent containing organic resin or metal element.

38. (New) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is attached onto a surface of the object to be processed while transferring the object and moving the droplet spraying means.

39. (New) A semiconductor manufacturing apparatus according to claim 9 further comprising a plurality of plasma generating means for performing a plasma treatment.

40. (New) A semiconductor manufacturing apparatus according to claim 37, wherein the plasma treatment is performed by the plurality of plasma generating means for forming a film over the object, etching the object, or ashing the object.